

Innovating Energy Technology

2MBI600VX-120-50

Power Module (V series) 1200V / 600A / 2-in-1 package

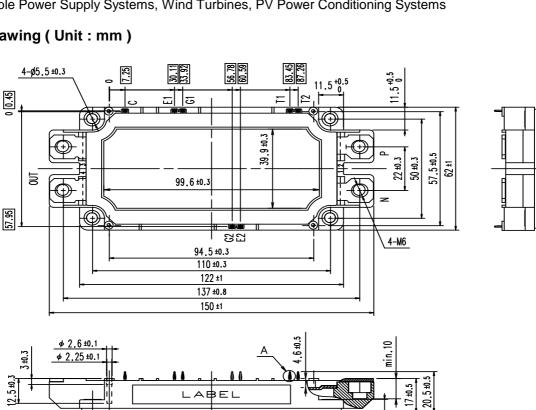
Features

Low V_{CE(sat)} Low Inductance Module structure Solderless press-fit terminals

Applications

Inverter for Motor Drives, AC and DC Servo Drives Uninterruptible Power Supply Systems, Wind Turbines, PV Power Conditioning Systems

■ Outline drawing (Unit : mm)

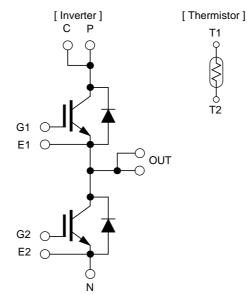


NOTE) MARKED SIDE WITH A TOLERANCE OF 4 00.5

Weight: 350g (typ.)

6.5±0.5

Equivalent Circuit



FM5F8402 2014/11







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IGBT Modules

■ Absolute Maximum Ratings (at T_c= 25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum Ratings	Units
Collector-Emitter voltage		V _{CES}			1200	V
Gate-Emitter voltage		V _{GES}			±20	V
		I	Continuous	T _C =25°C	750	
Collector current		Ι _C	Continuous	$T_{C}=100^{\circ}C$	600]
		l _c pulse	1ms		1200	A
		-I _C			600	
		-I _C pulse	1ms		1200	
Collector power dissipation		P _C	1 device		3750	W
Junction temperature		Tj			175	
Operating junction temperature		T _{jop}			150	°C
(under switching conditions)						
Case temperature		T _c			125	
Storage temperature		T _{stg}			-40 ~ 125	
Isolation	between terminal and copper base (*1)	V	AC: 1min.		2500	VAC
voltage	between thermistor and others (*2)	V _{iso}	AC. Imin.		2500	VAC
Screw	Mounting (*3)	-			3.5	Nm
Torque	Terminals (*4)	-			4.5	

(*1) All terminals should be connected together during the test.

(*2) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*3) Recommendable Value : 2.5-3.5 Nm (M5)

(*4) Recommendable Value : 3.5-4.5 Nm (M6)



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Electrical characteristics (at T_j= 25°C unless otherwise specified)

ltomo	Cumb ala	Conditions		Characteristics			
Items	Symbols			min.	typ.	max.	Units
Zero gate voltage Collector current	I _{CES}	V _{GE} =0V, V _{CE} =1200V		-	-	3.0	mA
Gate-Emitter leakage current	I _{GES}	V _{CE} =0V, V _{GE} =±20V		-	-	600	nA
Gate-Emitter threshold voltage	$V_{\text{GE(th)}}$	V _{CE} =20V, I _C =600mA		6.0	6.5	7.0	V
	N/		T _j =25°C	-	2.65	3.10	- V
	V _{CE(sat)} (terminal)	V _{GE} = 15V	T _j =125°C	-	3.00	-	
Collector-Emitter			T _j =150°C	-	3.05	-	
saturation voltage	V _{CE(sat)} (chip)	I _C = 600A	T _i =25°C	-	1.85	2.30	
			T _i =125°C	-	2.20	-	
			T _i =150°C	-	2.25	-	
Internal gate resistance	R _{G(int)}	-		-	1.25	-	Ω
Input capacitance	C _{ies}	V _{CE} =10V, V _{GE}	=0V, f=1MHz	-	48	-	nF
	t _{on}			-	550	-	
Turn-on time	t _r	V _{CC} = 600V	I _C = 600A	-	180	-	nsec
	t _{r(i)}	$V_{GE} = \pm 15V$	R _G = 0.62Ω	-	120	-	
Turn-off time	t _{off}	L _s = 80nH		-	1050	-	
	t _f			-	110	-	
	N/	V _{GE} = 0V	T _j =25°C	-	2.50	3.00	- V
	V _F		T _j =125°C	-	2.65	-	
	(terminal)		T _j =150°C	-	2.60	-	
Forward on voltage	V _F (chip)	I _F = 600A	T _j =25°C	-	1.70	2.15	
			T _j =125°C	-	1.85	-	
			T _i =150°C	-	1.80	-	
Reverse recovery time	t _{rr}	I _F = 600A		-	200	-	nsec
Thermistor Resistance	R	T=25°C T=100°C		-	5000	-	Ω
THEITHISION RESISIONCE	ĸ			465	495	520	
Thermistor B value	В	T=25/50°C		3305	3375	3450	K

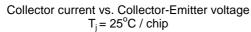
5. Thermal resistance characteristics

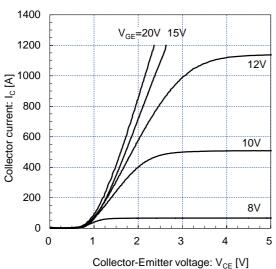
Items	Symbols	Conditions	Characteristics			Units
items	Symbols	Conditions	min.	typ.	max.	Units
Thermal resistance	P	IGBT	-	-	0.04	
(1device)	R _{th(j-c)}	FWD	-	-	0.06	°C/W
Contact thermal resistance (1device) (*1) Rth(c-f)		with thermal compound	-	0.0167	-	C/VV

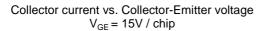
(*1) This is the value which is defined mounting on the additional cooling fin with thermal compound.

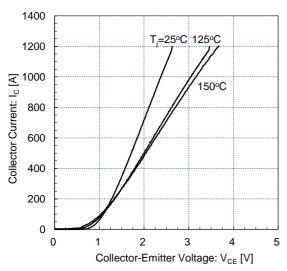


IGBT Modules

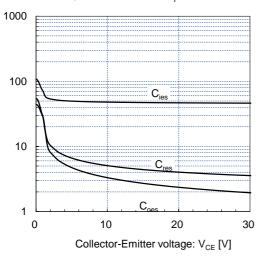


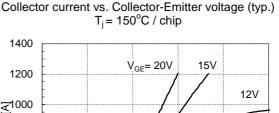


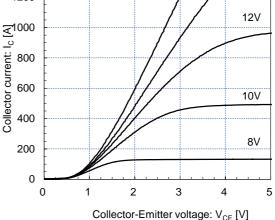




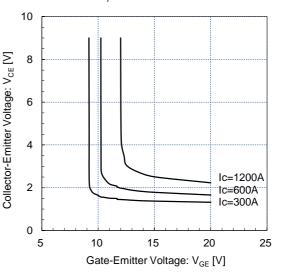


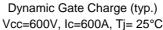


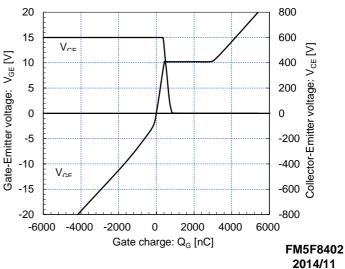




Collector-Emitter voltage vs. Gate-Emitter voltage $T_i = 25^{\circ}C / chip$



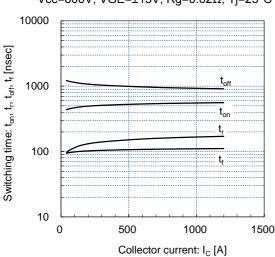






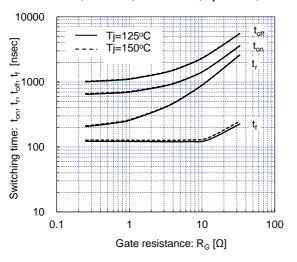
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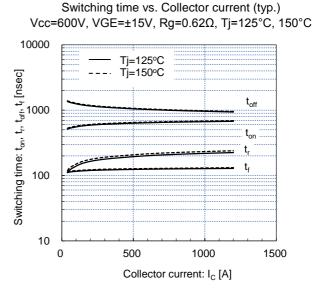


Switching time vs. Collector current (typ.) Vcc=600V, VGE= \pm 15V, Rg=0.62 Ω , Tj=25°C

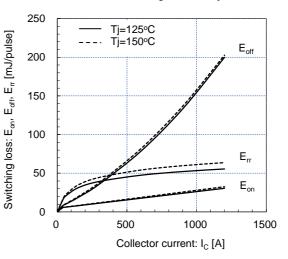
Switching time vs. Gate resistance (typ.) /cc=600V, Ic=600A, VGE=±15V, Tj=125°C, 150°(



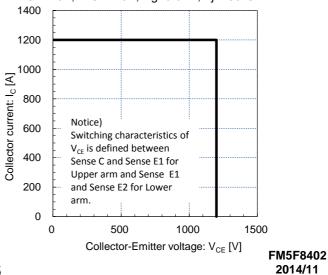
Switching loss vs. Gate resistance (typ.) /cc=600V, Ic=600A, VGE=±15V, Tj=125°C, 150°(400 Tj=125°C , E_{rr} [mJ/pulse] Tj=150°C ш¹200 Eof Switching loss: Eon, 00 Ε, 0 0 1 10 100 Gate resistance: $R_G [\Omega]$



Switching loss vs. Collector current (typ.) Vcc=600V, VGE=±15V, Rg=0.62Ω, Tj=125°C, 150°C



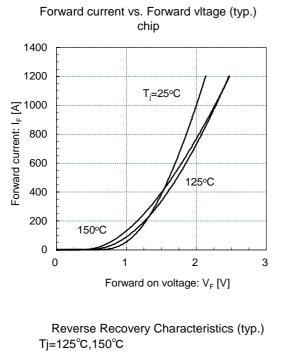
Reverse bias safe operating area (max.) +VGE=15V, -VGE=15V, Rg=0.62Ω, Tj=150°C

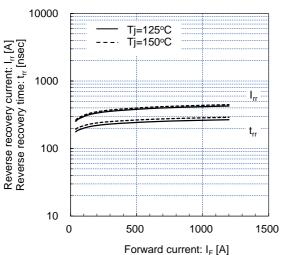


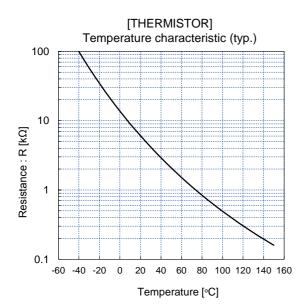
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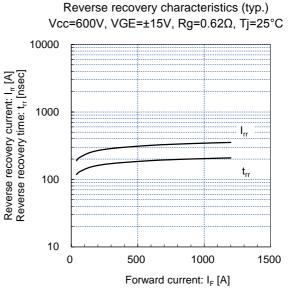


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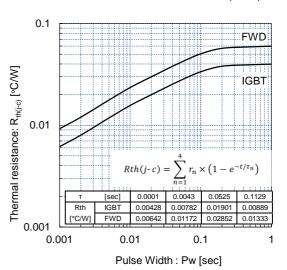


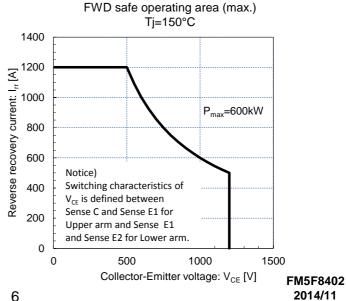






Transient Thermal Resistance (max.)







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